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Date: 1 8 0 9

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Application Number	10/026,019
Filing Date	December 27, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02674 US

<input checked="" type="checkbox"/>	SEKIGUCHI, S., et al., "Long wavelength GaInAsP/InP laser with n-n contacts using AlAs/InP hole injecting tunnel junction", article, Japanese Journal of Applied Physics, Part 2, No. 48, 04-15-1999, pgs L443-5.
<input type="checkbox"/>	STARCK, C., "Long wavelength VCSEL with tunnel junction and metamorphic AlAs/GaAs conductive DBR", article, Physics Review B, Vol 39, No 9, 01-15-1989, pgs 1871-83.
<input type="checkbox"/>	SUGIMOTO, M., et al., "Surface emitting devices with distributed Bragg reflectors grown by highly precise molecular beam epitaxy", article, Journal of Crystal Growth, Vol 127, 1996, pgs 1-4.
<input type="checkbox"/>	UCHIDA, T., et al., "CBE grown 1.5 μ m GaInAsP/InP surface emitting lasers", article, IEEE Journal of Quantum Electronics, Vol 29, No 6, June 1993, pgs 1975-80.
<input type="checkbox"/>	VAN DE WALLE, G., "Band lineups and deformation potentials in the model-solid theory", article, Physical Review B, Vol 39, No 3, 01-15-1989, pgs 1871-83.
<input type="checkbox"/>	WATKINS, T., "Long wavelength VCSELs move closer to reality", article, Compound Semiconductor, July 2000, pgs 65-7.
<input type="checkbox"/>	YAMADA, M., et al., "Low-threshold lasing at 1.3 μ m from GaAsSb quantum wells directly grown on GaAs substrates", article, IEEE, 0-7803-4947, 04/050, pgs 149-50.
<input type="checkbox"/>	YAMADA, M., et al., "Room temperature low-threshold CW operation of 1.23 μ m GaAsSb VCSELs on GaAs substrates", article, Electronics Letters, 03-30-2000, Vol 36, No 7, pgs B37-B38.
<input type="checkbox"/>	YANG, X., et al., "High performance 1.3 μ m InGaAsP:SbGaAs quantum well lasers grown by molecular beam epitaxy", journal article, journal of Vacuum Science and Technology B Microelectronics and Nanometer Structures, Vol. 18, No 3, Oct 1999, pgs 1484-7.
<input type="checkbox"/>	YANG, X., et al., "InGaAsNSb/GaAs quantum wells for 1.65 μ m lasers grown by molecular-beam epitaxy", article, Applied Physics Letters, Vol 79, No 26, pgs 4059-70.
<input type="checkbox"/>	YANO, M., et al., "Time-resolved reflection high energy electron diffraction analysis for atomic layer deposition of Ge/Si by molecular beam epitaxy", article, Journal of Crystal Growth, Vol 146, 1995, pgs 349-53.
<input type="checkbox"/>	YUEN, W., et al., "High-performance 1.6 μ m single-epitaxy top-emitting VCSEL", article, Electronics Letters, Vol 36, No 13, 06-22-2000, pgs 1121-3.

Examiner Signature		Date Considered	07/04/04
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EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

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